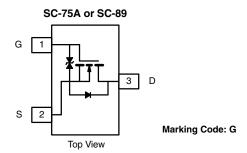


## N-Channel 1.5 V (G-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (mA)			
20	5 at $V_{GS} = 4.5 \text{ V}$	200			
	7 at $V_{GS} = 2.5 \text{ V}$	175			
	9 at V <sub>GS</sub> = 1.8 V	150			
	10 at V <sub>GS</sub> = 1.5 V	50			



#### **Ordering Information:**

Si1032R-T1-GE3 (SC-75A, Lead (Pb)-free and Halogen-free) Si1032X-T1-GE3 (SC-89, Lead (Pb)-free -free Halogen-free)

### **FEATURES**

- Halogen-free According to IEC 61249-2-21
  Definition
- Low-Side Switching
- Low On-Resistance: 5  $\Omega$
- Low Threshold: 0.9 V (typ.)
- Fast Switching Speed: 35 ns
- TrenchFET<sup>®</sup> Power MOSFETs: 1.5 V Rated
- 2000 V ESD Protection
- · Compliant to RoHS Directive 2002/95/EC

#### **BENEFITS**

- · Ease in Driving Switches
- · Low Offset (Error) Voltage
- · Low-Voltage Operation
- High-Speed Circuits
- · Low Battery Voltage Operation

## **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Load/Power Switching Cell Phones, Pagers

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)							
Parameter		Symbol	Si1032R		Si1032X		
			5 s	Steady State	5 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	20			V	
Gate-Source Voltage		$V_{GS}$	± 6				
0 " 0 1/T 15000	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	200	140	210	200	A
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C		110	100	150	140	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	500		600		mA
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	250	200	300	240	
	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	280	250	340	300	mW
Maximum Power Dissipation <sup>a</sup> for SC-75	T <sub>A</sub> = 85 °C		145	130	170	150	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150			•	°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000			V	

#### Notes:

a. Surface mounted on FR4 board.

ROHS COMPLIANT HALOGEN FREE

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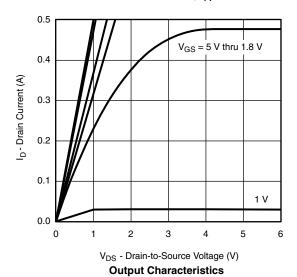
<b>SPECIFICATIONS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.40	0.7	1.2	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 2.8 \text{ V}$		± 0.5	± 1.0		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 1.0	± 3.0	μΑ	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1		
	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	250			mA	
		$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$			5	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 175 \text{ mA}$			7		
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 1.8 \text{ V}, I_D = 150 \text{ mA}$			9		
		$V_{GS} = 1.5 \text{ V}, I_D = 40 \text{ mA}$			10		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$		0.5		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 150 mA, V <sub>GS</sub> = 0 V			1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			750			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 250 \text{ mA}$		75		рC	
Gate-Drain Charge	$Q_{gd}$			225			
Turn-On Delay Time	t <sub>d(on)</sub>				50		
Rise Time	t <sub>r</sub>	$V_{DD} = 10 \text{ V, R}_{L} = 47 \Omega$			25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong \text{200 mA},~\text{V}_\text{GEN}=\text{4.5 V},~\text{R}_\text{g}=\text{10}~\Omega$			50	ns	
Fall Time	t <sub>f</sub>				25		

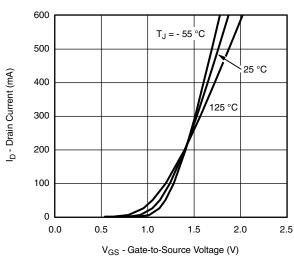
#### Notes:

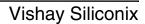
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

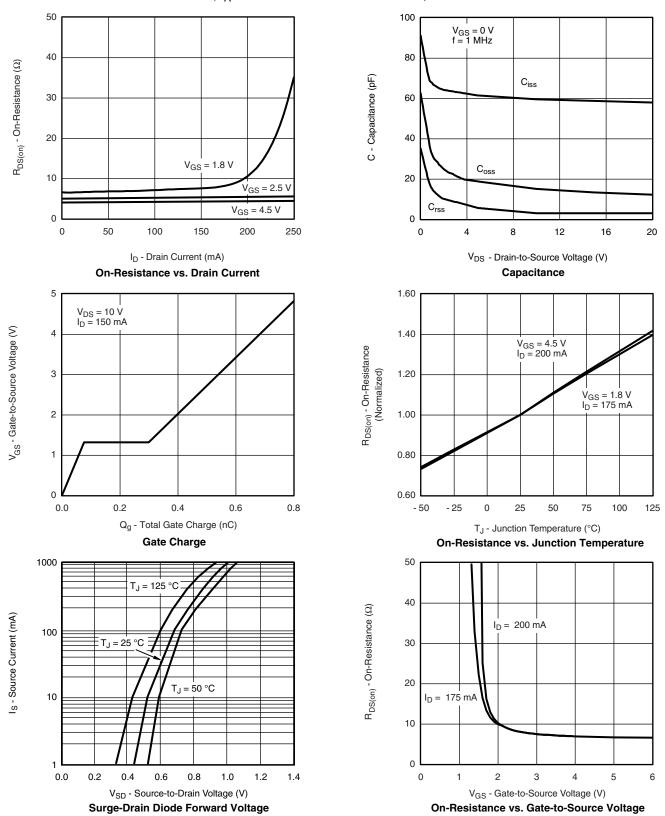








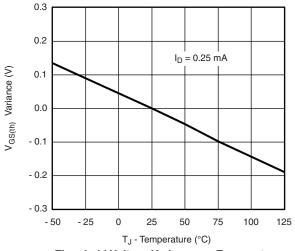
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

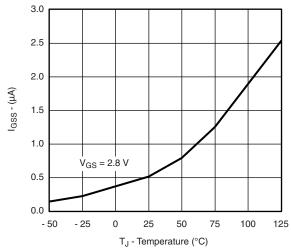


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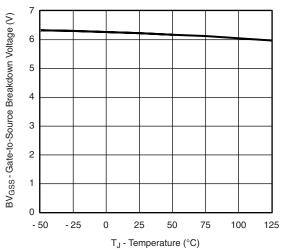
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



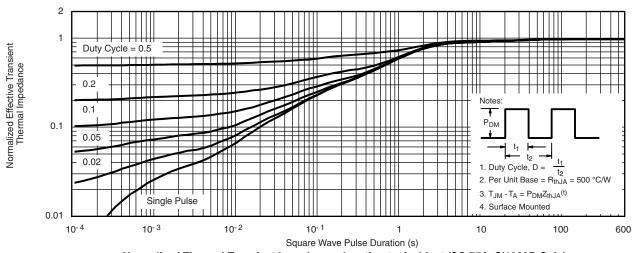


Threshold Voltage Variance vs. Temperature





BV<sub>GSS</sub> vs. Temperature

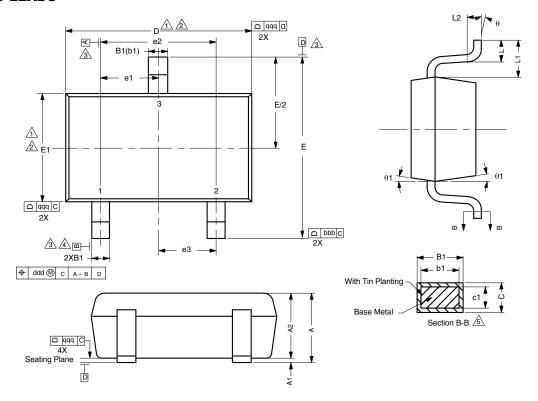


Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A, Si1032R Only)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71172">www.vishay.com/ppg?71172</a>.



### **SC-75A: 3-LEADS**



#### **Notes**

Dimensions in millimeters will govern.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interelead flash, but including any mismatch between the top and bottom of the plastic body.

2 Datums A, B and D to be determined 0.10 mm from the lead tip.

4 Terminal positions are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTE
Α	-	-	0.80	
A <sub>1</sub>	0.00	-	0.10	
A <sub>2</sub>	0.65	0.70	0.80	
B <sub>1</sub>	0.19	-	0.24	5
b <sub>1</sub>	0.17	-	0.21	
С	0.13	-	0.15	5
C <sub>1</sub>	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E <sub>1</sub>	0.66	0.76	0.86	1, 2
e <sub>1</sub>		0.50 BSC		
e <sub>2</sub>	1.00 BSC			
e <sub>3</sub>	0.50 BSC			
L	0.15	0.205	0.30	
L <sub>1</sub>	0.40 REF			
L <sub>2</sub>	0.15 BSC			
θ	0°	-	8°	
$\theta_1$	4°	-	10°	
ECN: E11-	2210-Rev. D,	08-Aug-11		

ECN: E11-2210-Rev. D, 08-Aug-11

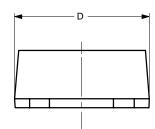
DWG: 5868

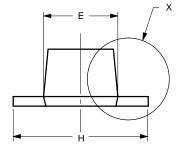


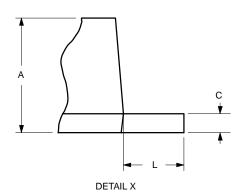


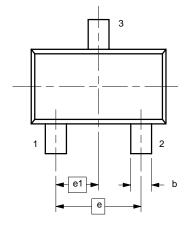
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## SC89-3





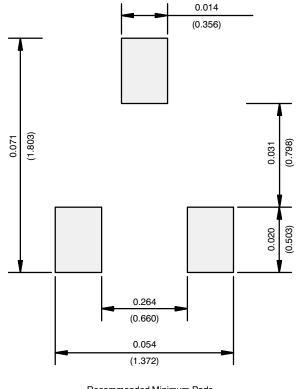




	MILLIM	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	0.60	0.80	0.024	0.031	
b	0.23	0.33	0.009	0.013	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
Е	0.75	0.95	0.030	0.037	
е	1.00 BSC		0.040	BSC	
e <sub>1</sub>	0.50 BSC		0.020	BSC	
Н	1.50	1.70	0.059	0.067	
L	0.30	0.50	0.012	0.020	



## **RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead**



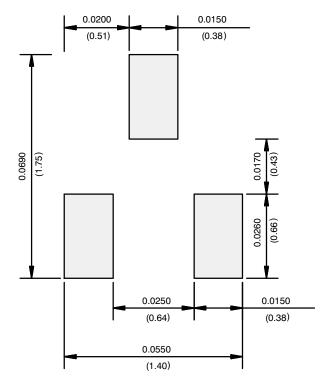
Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



## **RECOMMENDED MINIMUM PADS FOR SC-89: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000